Abstracts

Designing high-power limiter circuits with GaAs PIN diodes

D.G. Smith, D.D. Heston and D.L. Allen. "Designing high-power limiter circuits with GaAs PIN diodes." 1999 MTT-S International Microwave Symposium Digest 99.1 (1999 Vol. I [MWSYM]): 329-332 vol.1.

The three key parameters of passive limiter circuits: limiting, burnout and insertion loss are explained in great detail in this paper. The limiting and burnout characteristics of various size GaAs PIN diodes have been measured. Results indicate that the burnout level is proportional to diode circumference. A design concept for a broadband high-power limiter is discussed using this measured data.

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